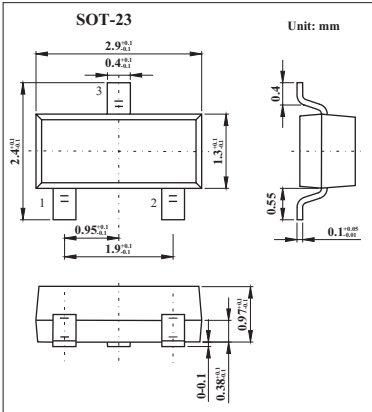


Schottky Barrier Diode
MMBD301

■ Features



■ Absolute Maximum Ratings $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Value	Unit
Working Inverse Voltage	W_{IV}	25	V
Forward Power Dissipation @ $T_a = 25^{\circ}\text{C}$	pF	200	mW
Derate above 25°C		2.0	mW/ $^{\circ}\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^{\circ}\text{C}$
Operating Junction Temperature	T_J	-55 to +125	$^{\circ}\text{C}$

■ Electrical Characteristics $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Breakdown Voltage	BV	$I_R = 10\ \mu\text{A}$	30		V
Reverse Leakage	I_R	$V_R = 25\text{ V}$		200	nA
Forward Voltage	V_F	$I_F = 1.0\text{ mA}$		450	mV
		$I_F = 10\text{ mA}$		600	
Capacitance	C_T	$V_R = 15\text{ V}, f = 1.0\text{ MHz}$		1.5	pF

■ Marking

Marking	4T
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